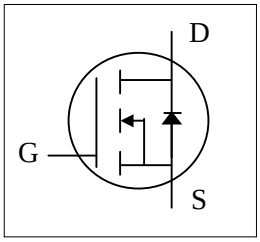
# AP50T10GM-HF

**Halogen-Free Product**

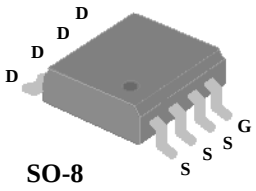
**Advanced Power Electronics Corp.**

*N-CHANNEL ENHANCEMENT MODE POWER MOSFET*

- ▼ **Low Gate Charge**
- ▼ **Simple Drive Requirement**
- ▼ **Surface Mount Package**
- ▼ **Halogen Free & RoHS Compliant Product**




| | |
|---|---|
| $BV_{DSS}$ | 100V |
| $R_{DS(ON)}$ | 30mΩ |
| $I_D$ | 6.5A |




**SO-8**

## Description

AP50T10 series are from Advanced Power innovated design and silicon process technology to achieve the lowest possible on-resistance and fast switching performance. It provides the designer with an extreme efficient device for use in a wide range of power applications.

The SO-8 package is widely preferred for all commercial-industrial surface mount applications using infrared reflow technique and suited for voltage conversion or switch applications.

## Absolute Maximum Ratings@$T_j$=25°C(unless otherwise specified)

| Symbol | Parameter | Rating | Units |
|---|---|---|---|
| $V_{DS}$ | Drain-Source Voltage | 100 | V |
| $V_{GS}$ | Gate-Source Voltage | ±20 | V |
| $I_D$@$T_A$=25℃ | Drain Current, $V_{GS}$ @ 10V[3] | 6.5 | A |
| $I_D$@$T_A$=70℃ | Drain Current, $V_{GS}$ @ 10V[3] | 5.2 | A |
| $I_{DM}$ | Pulsed Drain Current[1] | 24 | A |
| $P_D$@$T_A$=25℃ | Total Power Dissipation | 2.5 | W |
| $T_{STG}$ | Storage Temperature Range | -55 to 150 | ℃ |
| $T_J$ | Operating Junction Temperature Range | -55 to 150 | ℃ |

## Thermal Data

| Symbol | Parameter | Value | Unit |
|---|---|---|---|
| Rthj-a | Maximum Thermal Resistance Junction-ambient[3] | 50 | ℃/W |

## Electrical Characteristics@$T_j$=25°C(unless otherwise specified)

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Units |
|---|---|---|---|---|---|---|
| $BV_{DSS}$ | Drain-Source Breakdown Voltage | $V_{GS}$=0V, $I_D$=250uA | 100 | - | - | V |
| $R_{DS(ON)}$ | Static Drain-Source On-Resistance[2] | $V_{GS}$=10V, $I_D$=6A | - | - | 30 | mΩ |
| | | $V_{GS}$=5V, $I_D$=4A | - | - | 70 | mΩ |
| $V_{GS(th)}$ | Gate Threshold Voltage | $V_{DS}$=$V_{GS}$, $I_D$=250uA | 1 | - | 3 | V |
| $g_{fs}$ | Forward Transconductance | $V_{DS}$=10V, $I_D$=6A | - | 12 | - | S |
| $I_{DSS}$ | Drain-Source Leakage Current | $V_{DS}$=80V, $V_{GS}$=0V | - | - | 25 | uA |
| $I_{GSS}$ | Gate-Source Leakage | $V_{GS}$= ±20V, $V_{DS}$=0V | - | - | ±100 | nA |
| $Q_g$ | Total Gate Charge | $I_D$=6A | - | 41 | 65 | nC |
| $Q_{gs}$ | Gate-Source Charge | $V_{DS}$=50V | - | 6 | - | nC |
| $Q_{gd}$ | Gate-Drain ("Miller") Charge | $V_{GS}$=10V | - | 15.5 | - | nC |
| $t_{d(on)}$ | Turn-on Delay Time | $V_{DS}$=50V | - | 10 | - | ns |
| $t_r$ | Rise Time | $I_D$=1A | - | 9.5 | - | ns |
| $t_{d(off)}$ | Turn-off Delay Time | $R_G$=3.3Ω | - | 37 | - | ns |
| $t_f$ | Fall Time | $V_{GS}$=10V | - | 19 | - | ns |
| $C_{iss}$ | Input Capacitance | $V_{GS}$=0V | - | 1810 | 2940 | pF |
| $C_{oss}$ | Output Capacitance | $V_{DS}$=15V | - | 250 | - | pF |
| $C_{rss}$ | Reverse Transfer Capacitance | f=1.0MHz | - | 190 | - | pF |
| $R_g$ | Gate Resistance | f=1.0MHz | - | 1.7 | 3.4 | Ω |

## Source-Drain Diode

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Units |
|---|---|---|---|---|---|---|
| $V_{SD}$ | Forward On Voltage[2] | $I_S$=1.9A, $V_{GS}$=0V | - | - | 1.3 | V |
| $t_{rr}$ | Reverse Recovery Time | $I_S$=6A, $V_{GS}$=0V | - | 40 | - | ns |
| $Q_{rr}$ | Reverse Recovery Charge | dI/dt=100A/μs | - | 70 | - | nC |

### Notes:

1.Pulse width limited by Max. junction temperature.

2.Pulse test

3.Surface mounted on 1 $in^2$ copper pad of FR4 board, t ≤10sec ; 125℃/W when mounted on min. copper pad.

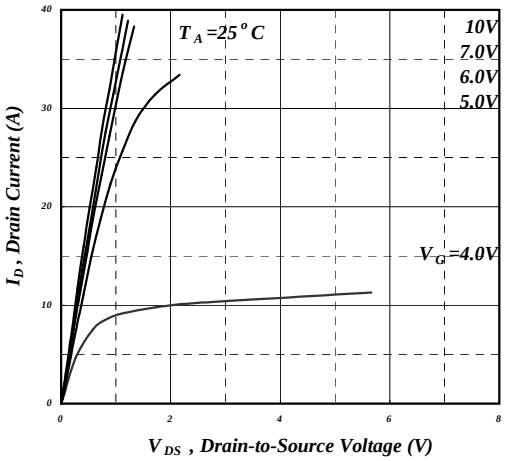



**Fig 1. Typical Output Characteristics**

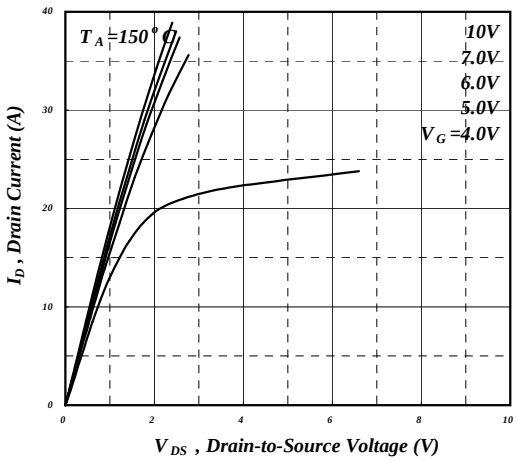



**Fig 2. Typical Output Characteristics**

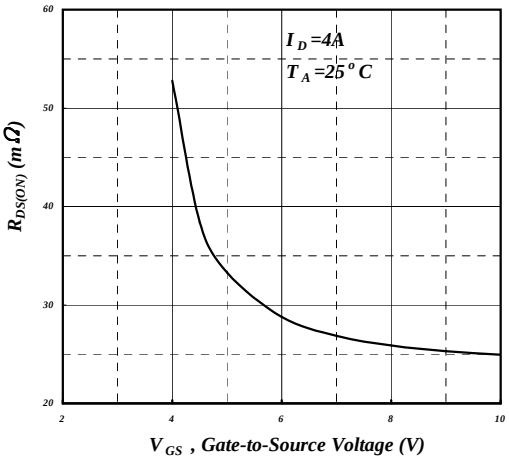



**Fig 3. On-Resistance v.s. Gate Voltage**

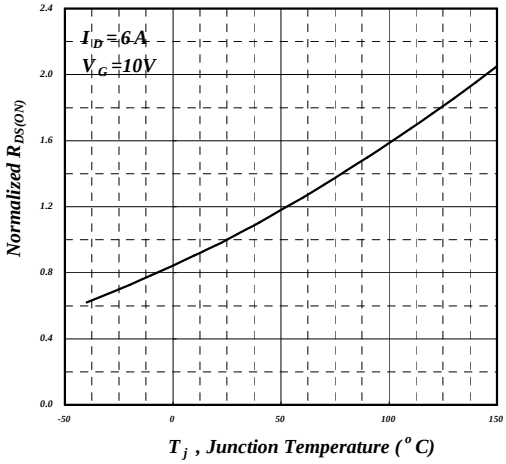



**Fig 4. Normalized On-Resistance v.s. Junction Temperature**

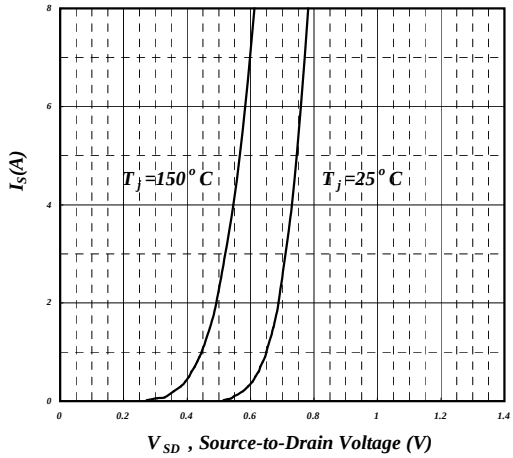



**Fig 5. Forward Characteristic of Reverse Diode**

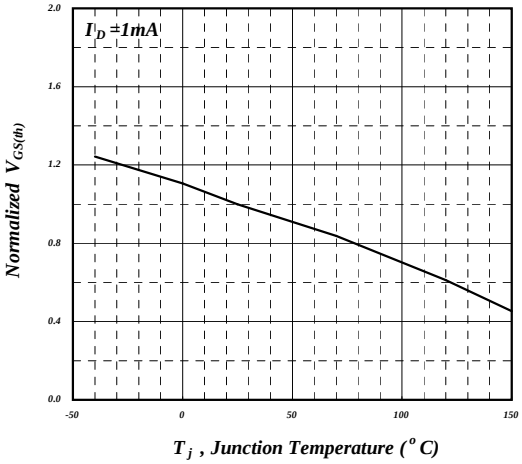



**Fig 6. Gate Threshold Voltage v.s. Junction Temperature**

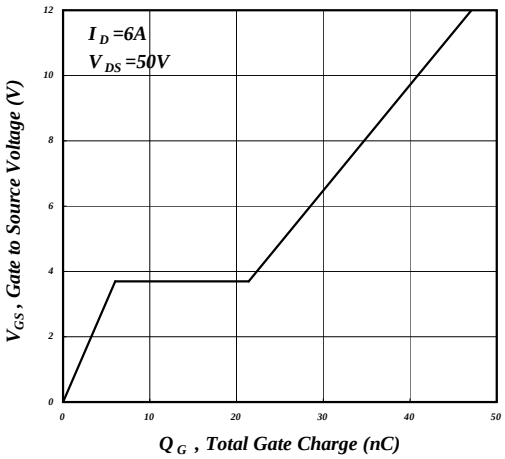



Fig 7. Gate Charge Characteristics

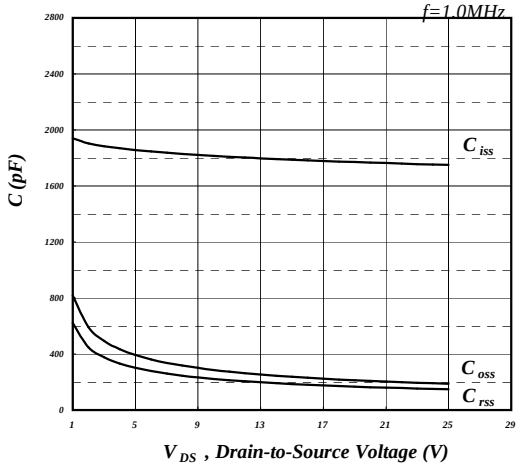



Fig 8. Typical Capacitance Characteristics

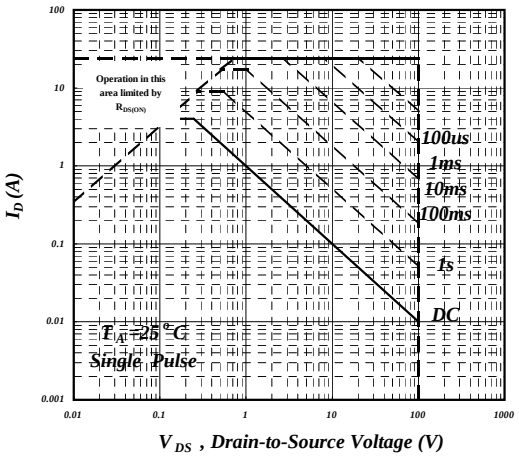



Fig 9. Maximum Safe Operating Area

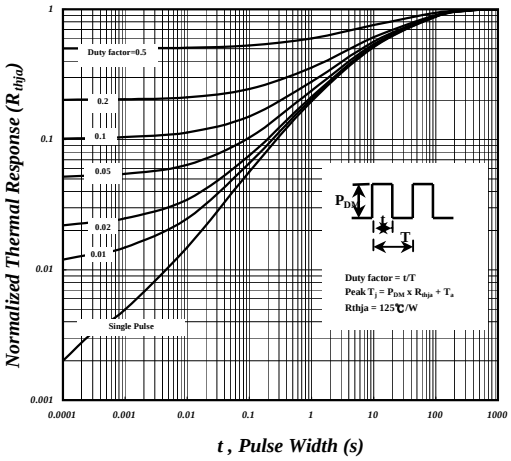



Fig 10. Effective Transient Thermal Impedance

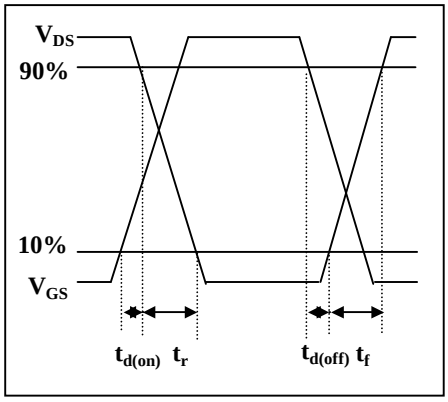



Fig 11. Switching Time Waveform

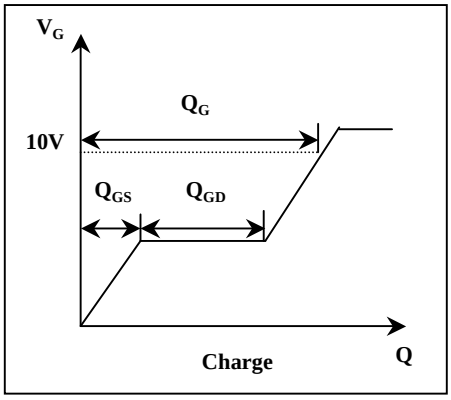



Fig 12. Gate Charge Waveform

## MARKING INFORMATION